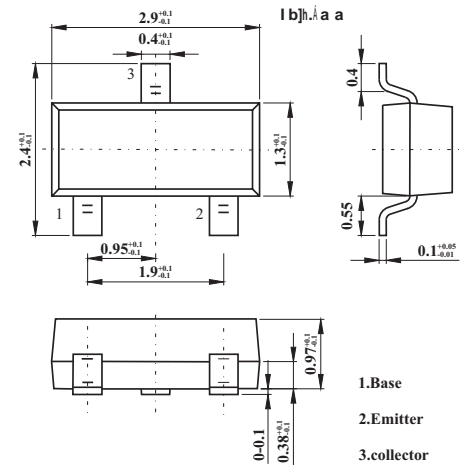


FEATURES

Low $V_{CE(sat)}$

High V_{CEO} , $V_{CEO}=80V$



Parameter	Symbol	Rating	Unit
Collector-base breakdown voltage	V_{CBO}	80	V
Collector-emitter breakdown voltage	V_{CEO}	80	V
Emitter-base breakdown voltage	V_{EBO}	5	V
Collector cutoff current	I_C	0.5	A
Collector power dissipation	P_C	0.2	W
Junction temperature	T	150	$^{\circ}C$
Storage temperature	T_{st}		$^{\circ}C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$B_{V_{CBO}}$	$I_C=50\mu A$	80			V
Collector-emitter breakdown voltage	$B_{V_{CEO}}$	$I_C=2mA$	80			V
Emitter-base breakdown voltage	$B_{V_{EBO}}$	$I_E=50\mu A$	5			V
Collector cutoff current	I_{CBO}	$V_{CB}=50V$			0.5	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=4V$			0.5	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C/I_B=500mA/50mA$		0.2	0.5	V
DC current transfer ratio	h_{FE}	$V_{CE}=3V, I_C=100mA$	120		390	
Output capacitance	f_T	$V_{CE}=10V, I_E=0-50mA, f=100MHz$		120		MHz
Transition frequency	f_{c2}	$n = V, I$				